improve the crystallinity of the side faces so as to improve the crystallinity of the second semiconductor layer 103 which crystal grows from at least the side faces. In such a case, the six angles of the hexagon that defines the outline of the depression 104 in the major surface of the first semiconductor layer 102 are, of course, all equal to 120 degrees.

IN THE CLAIMS:

Please amend claims 17, 18, 44, 49, and 52 as follows:

17. (Amended) A method for the manufacture of a semiconductor device comprising:

a step of preparing a substrate in which a surface thereof is formed a depression having a triangle or hexagonal figure when viewed from the substrate normal; and

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure, whereby said depression is filled by said semiconductor layer,

wherein said depression forming step is performed such that an inside face of said depression is defined by either a plane having a plane orientation of (1, -1, 0, n), where said number n is an arbitrary number other than 0, or its equivalent plane.

18. (Amended) A method for the manufacture of a semiconductor device comprising:

a step of preparing a substrate;

a step of forming on a surface of said substrate a depression having a triangle or hexagonal figure when viewed from the substrate normal; and

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure, whereby said depression is filled by said semiconductor layer,

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wherein said depression forming step is performed such that an inside face of said depression is defined by either a plane having a plane origination of (1, -1, 0, n), where said number n is an arbitrary number other than 0, or its equivalent plane.

44. (Amended) A method for the manufacture of a semiconductor substrate including:

a step of preparing a substrate for crystal growth;

a step of depositing on said crystal growth substrate a first semiconductor layer having a hexagonal crystal structure;

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a step of exposing either a plane having a plane orientation of (1, -1, 0, n) where said number n is an arbitrary number, or its equivalent plane by subjecting a part of said first semiconductor layer to an etching process; and

after said exposing step, a step of depositing on said first semiconductor layer a second semiconductor layer having a hexagonal crystal structure, whereby said plane is covered with said second semiconductor layer.

49. (Amended) A method for the manufacture of a semiconductor substrate comprising:

a step of forming a substrate having on a surface thereof a depression having a triangle or hexagonal figure when viewed from the substrate normal;

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a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure, whereby said structure is filled by said semiconductor layer; and

a step of taking out said semiconductor layer by removal of said substrate,

wherein said depression has an inside face defined by either a plane having a plane orientation of (1, -1, 0, n), where said number n is an arbitrary number other than 0, or its equivalent plane.

52. (Amended) A method for the manufacture of a semiconductor substrate comprising:

a step of forming a substrate having on a surface thereof a triangle or hexagonal

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projection;

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure, whereby said projection is capped with said semiconductor layer; and

a step of taking out said semiconductor layer by removal of said substrate,

wherein said projection has a side face defined by either a plane having a plane orientation of (1, -1, 0, n), wherein said number n is an arbitrary number other than 0, or its equivalent plane.